

UTC2SA684 PNP EPITAXIAL PLANAR TRANSISTOR

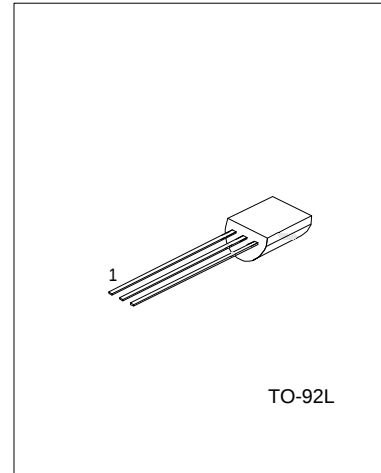
PNP EPITAXIAL PLANAR TRANSISTOR

DESCRIPTION

The UTC 2SA684 is power amplifier and driver.

FEATURES

- *Automatic insertion by radial tapping possible.
- *Complementary pair with 2SC1384



1:EMITTER 2:COLLECTOR 3:BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	VCBO	60	V
Collector-Emitter Voltage	VCEO	50	V
Emitter-Base Voltage	VEBO	5	V
Peak Collector Current	Icp	1.5	A
Collector Current(DC)	Ic	1	A
Collector Dissipation(Ta=25°C)	Pc	1	W
Junction Temperature	Tj	150	°C
Storage Temperature	TSTG	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS(Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cut-Off Current	ICBO	VCB=20V, IE=0			0.1	μA
Collector-Base Voltage	VCBO	Ic=10μA, IE=0	60			V
Collector-Emitter Voltage	VCEO	Ic=2mA, IB=0	50			V
Emitter-Base Voltage	VEBO	IE=10μA, IC=0	5			V
DC Current Gain	hFE1 hFE2	VCE=10V, Ic=500mA VCE=5V, IB=1A	85 50		340	
Collector-Emitter Saturation Voltage	VCE(sat)	Ic=0.5A, IB=50mA		0.2	0.4	V
Base-Emitter Saturation Voltage	VBE(sat)	Ic=0.5A, IB=50mA		0.85	1.2	V
Current Gain Bandwidth Product	fr	VCE=10V, IB=50mA, f=200MHz		200		MHz
Output Capacitance	Cob	VCB=10V, IE=0, f=1MHz		20	30	pF

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CLASSIFICATION OF hFE

RANK	Q	R	S
RANGE	85-170	120-240	170-340

TYPICAL PERFORMANCE CHARACTERISTICS